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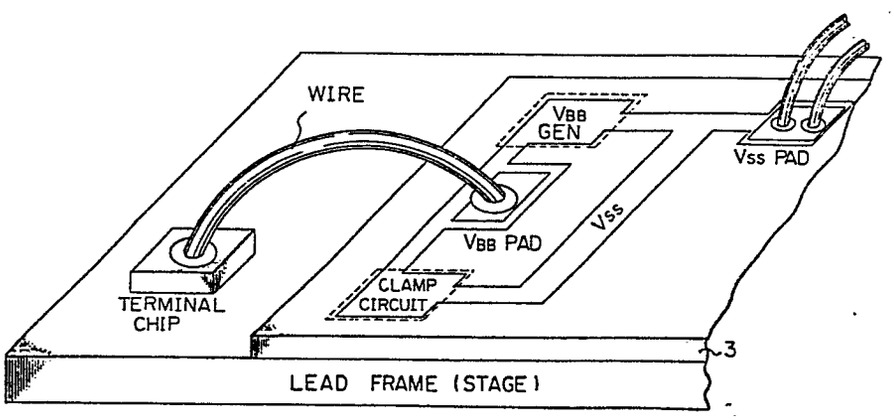
(54) **Semiconductor circuit device.**

(57) A semiconductor circuit device including: a semiconductor substrate (3), a plurality of metal oxide semiconductor (MOS) transistors formed on the semiconductor substrate, a plurality of ground side power source lines (V_{SS}) formed on the semiconductor substrate, a back gate bias generating circuit (V_{BB}GEN) formed between the substrate and the ground side power source line, for supplying a back gate voltage to the substrate, and a clamp circuit consisting of a MOS diode formed on the substrate and provided between the substrate and the ground side power source line, for clamping the potential of the substrate to a predetermined level when the back gate bias generating circuit is not operated.

Fig. 11



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EUROPEAN SEARCH REPORT

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Application number

EP 86 30 0240

DOCUMENTS CONSIDERED TO BE RELEVANT

Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int. Cl.4)
X	EP-A-0 024 903 (FUJITSU) * Abstract; figure 2 *	1,2	G 05 F 3/20
X	PATENTS ABSTRACTS OF JAPAN, vol. 6, no. 107 (E-113)[985], 17th June 1982; & JP - A - 57 39 566 (TOKYO SHIBAURA DENKI K.K.) 04-03-1982 * Whole document *	1	
A	US-A-3 794 862 (ROCKWELL) * Abstract; figure 1 *	1	
A	IEEE JOURNAL OF SOLID-STATE CIRCUITS, vol. SC-15, no. 5, October 1980, pages 839-846, IEEE, New York, US; J.Y. CHAN et al.: "A 100 ns 5 V only 64K x 1 MOS dynamic RAM" * Page 842, figure 6 *	1	

TECHNICAL FIELDS SEARCHED (Int. Cl.4)

G 05 F 3/00
H 02 M 3/00
H 01 L 27/00

The present search report has been drawn up for all claims

Place of search	Date of completion of the search	Examiner
THE HAGUE	25-08-1986	ZAEGEL B.C.

CATEGORY OF CITED DOCUMENTS

X : particularly relevant if taken alone
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